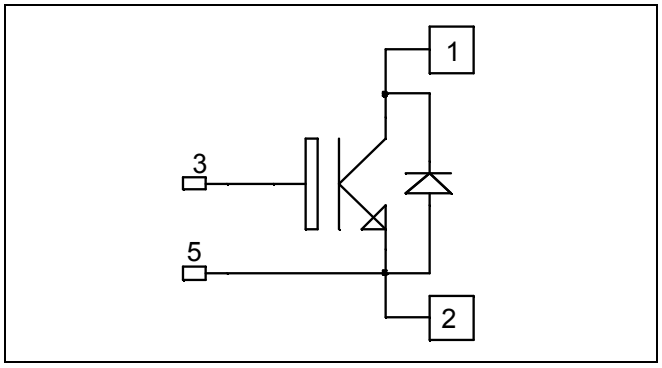
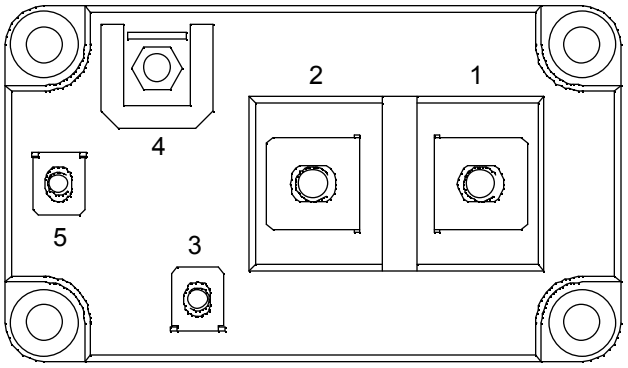
APTGF500U60D4

Single switch NPT IGBT Power Module

V_{CES} = 600V
I_C = 500A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
  - M6 connectors for power
  - M4 connectors for signal
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	625	A
		T_C = 80°C	500	
I_{CM}	Pulsed Collector Current	T_C = 25°C	900	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	2000	W
RBSOA	Reverse Bias Safe Operation Area	T_j = 125°C	900A@520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V	T_j = 25°C		1	500	µA
			T_j = 125°C		1		mA
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} = 15V, I_C = 500A	T_j = 25°C		1.95	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 6mA		4.5	5.5	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V, V_{CE} = 25V f = 1MHz		26		nF
C_{res}	Reverse Transfer Capacitance			2.4		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V, V_{Bus} = 300V, I_C = 600A, R_G = 4.7Ω		174		ns
T_r	Rise Time			80		
$T_{d(off)}$	Turn-off Delay Time			400		
T_f	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V, V_{Bus} = 300V, I_C = 600A, R_G = 4.7Ω		200		ns
T_r	Rise Time			85		
$T_{d(off)}$	Turn-off Delay Time			420		
T_f	Fall Time			80		
E_{on}	Turn on Energy			11		mJ
E_{off}	Turn off Energy			22		

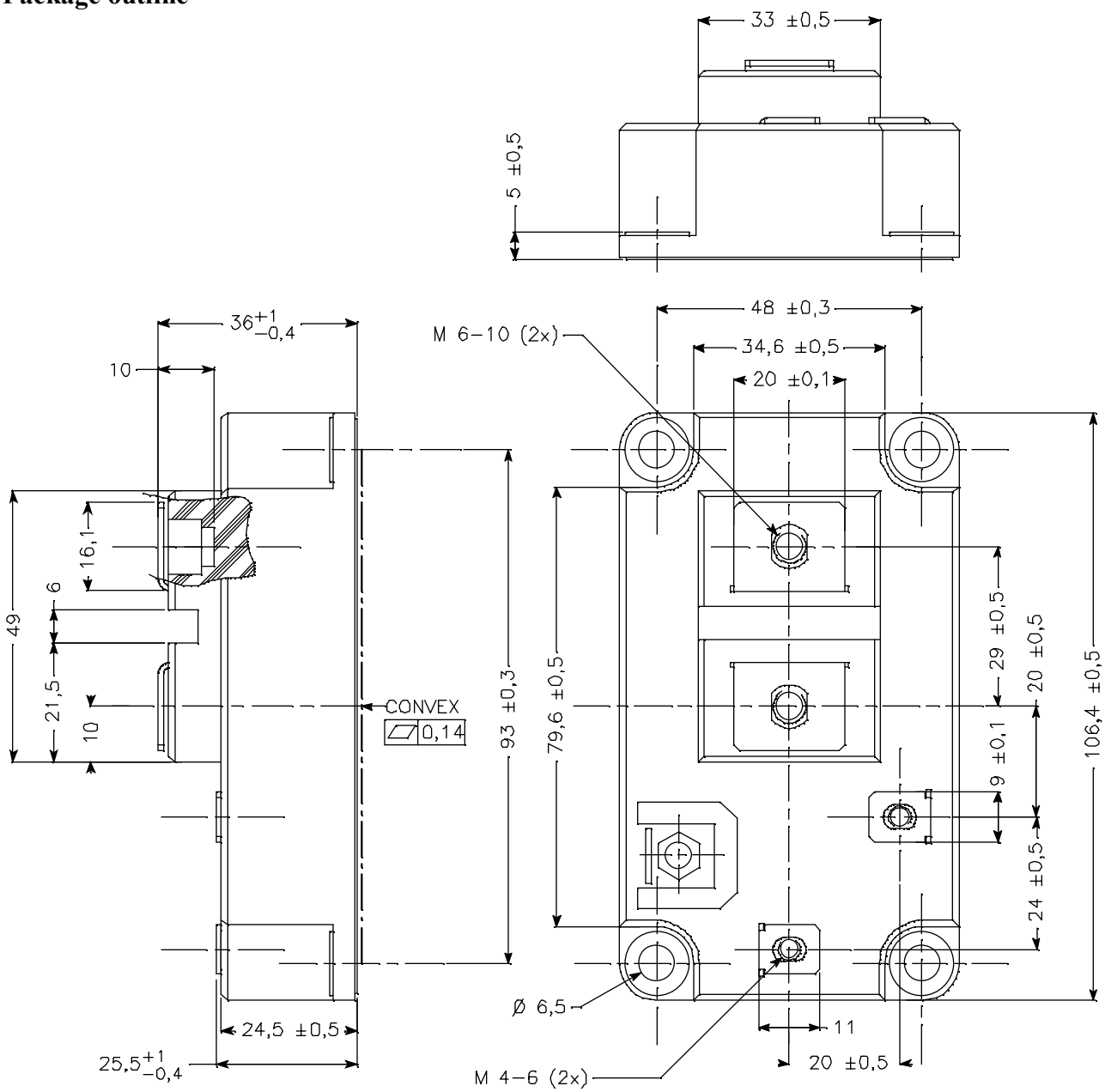
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_F	Diode Forward Voltage	I_F = 600A, V_{GE} = 0V	T_j = 25°C		1.25	1.6	V
			T_j = 125°C		1.2		
Q_{rr}	Reverse Recovery Charge	I_F = 600A, V_R = 300V, di/dt =5600A/µs	T_j = 25°C		40		µC
			T_j = 125°C		66		

Thermal and package characteristics

Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case	IGBT			0.06	°C/W
		Diode			0.12	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	°C
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		125	
Torque	Mounting torque	M6	3		5	N.m
		M4	1		2	
Wt	Package Weight				420	g

Package outline



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.